

# **LDO Voltage Regulator** -

# Adjustable Output, Load Dump Protection

60 V, 100 mA

# **LM2931, NCV2931 Series**

The LM2931 series consists of positive fixed and adjustable output voltage regulators that are specifically designed to maintain proper regulation with an extremely low input-to-output voltage differential. These devices are capable of supplying output currents in excess of 100 mA and feature a low bias current of 0.4 mA at 10 mA output.

Designed primarily to survive in the harsh automotive environment, these devices will protect all external load circuitry from input fault conditions caused by reverse battery connection, two battery jump starts, and excessive line transients during load dump. This series also includes internal current limiting, thermal shutdown, and additionally, is able to withstand temporary power—up with mirror—image insertion.

Due to the low dropout voltage and bias current specifications, the LM2931 series is ideally suited for battery powered industrial and consumer equipment where an extension of useful battery life is desirable. The 'C' suffix adjustable output regulators feature an output inhibit pin which is extremely useful in microprocessor–based systems.

#### Features

- Input-to-Output Voltage Differential of < 0.6 V @ 100 mA
- Output Current in Excess of 100 mA
- Low Bias Current
- 60 V Load Dump Protection
- -50 V Reverse Transient Protection
- Internal Current Limiting with Thermal Shutdown
- Temporary Mirror-Image Protection
- Ideally Suited for Battery Powered Equipment
- Economical 5-Lead TO-220 Package with Two Optional Leadforms

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- Available in Surface Mount SOP-8, D<sup>2</sup>PAK and DPAK Packages
- High Accuracy (±2.5%) Reference (LM2931AC) Available
- NCV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q100 Qualified and PPAP Capable
- Pb-Free Packages are Available

#### **Applications**

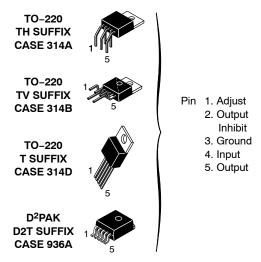
- Battery Powered Consumer Products
- Hand-held Instruments
- Camcorders and Cameras

#### **FIXED OUTPUT VOLTAGE**

TO-92 Pin 1. Output **Z SUFFIX** 2. Ground CASE 29-10 3. Input TO-220 T SUFFIX CASE 221AB **DPAK DT SUFFIX** Pin 1. Input CASE 369C 2. Ground 3. Output D<sup>2</sup>PAK **D2T SUFFIX CASE 936** SOT-223 ST SUFFIX

#### ADJUSTABLE OUTPUT VOLTAGE

**CASE 318H** 

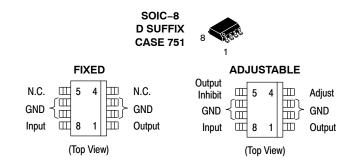


#### **ORDERING INFORMATION**

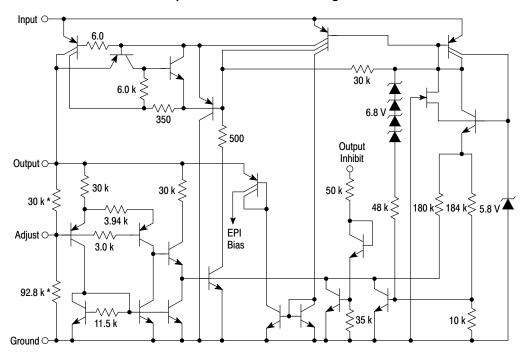
See detailed ordering and shipping information on page 12 of this data sheet.

#### **DEVICE MARKING INFORMATION**

See general marking and heatsink information in the device marking section on page 14 of this data sheet.



#### **Representative Schematic Diagram**



<sup>\*</sup>Deleted on Adjustable Regulators

This device contains 26 active transistors.

#### **MAXIMUM RATINGS**

Rating	Symbol	Value	Unit
Input Voltage Continuous	VI	40	Vdc
Transient Input Voltage (τ ≤ 100 ms)	$V_I(\tau)$	60	Vpk
Transient Reverse Polarity Input Voltage 1.0% Duty Cycle, τ ≤ 100 ms	$-V_{I}(\tau)$	-50	Vpk
Electrostatic Discharge Sensitivity (ESD) Human Body Model (HBM) Class 2, JESD22 A114-C Machine Model (MM) Class A, JESD22 A115-A Charged Device Model (CDM), JESD22 C101-C	- - -	2000 200 2000	V V
Power Dissipation Case 29 (TO–92 Type) T <sub>A</sub> = 25°C Thermal Resistance, Junction–to–Ambient Thermal Resistance, Junction–to–Case Case 221A, 314A, 314B and 314D (TO–220 Type)	P <sub>D</sub> R <sub>θJA</sub> R <sub>θJC</sub>	Internally Limited 178 83	W °C/W °C/W
T <sub>A</sub> = 25°C Thermal Resistance, Junction–to–Ambient Thermal Resistance, Junction–to–Case Case 318H (SOT–223)	P <sub>D</sub> R <sub>θJA</sub> R <sub>θJC</sub>	Internally Limited 65 5.0	W °C/W °C/W
T <sub>A</sub> = 25°C Thermal Resistance, Junction-to-Ambient Thermal Resistance, Junction-to-Case	P <sub>D</sub> R <sub>θJA</sub> R <sub>θJC</sub>	Internally Limited 242 21	W °C/W °C/W
Case 369A (DPAK) (Note 1)  T <sub>A</sub> = 25°C  Thermal Resistance, Junction-to-Ambient  Thermal Resistance, Junction-to-Case	P <sub>D</sub> R <sub>θJA</sub> R <sub>θ</sub> JC	Internally Limited 92 6.0	W °C/W °C/W
Case 751 (SOP-8) (Note 2)  T <sub>A</sub> = 25°C  Thermal Resistance, Junction-to-Ambient  Thermal Resistance, Junction-to-Case	P <sub>D</sub> R <sub>θJA</sub> R <sub>θJC</sub>	Internally Limited 160 25	W °C/W °C/W
Case 936 and 936A (D <sup>2</sup> PAK) (Note 3)  T <sub>A</sub> = 25°C  Thermal Resistance, Junction-to-Ambient  Thermal Resistance, Junction-to-Case	P <sub>D</sub> R <sub>θ</sub> JA R <sub>θ</sub> JC	Internally Limited 70 5.0	W °C/W °C/W
Operating Ambient Temperature Range	T <sub>A</sub>	-40 to +125	°C
Operating Die Junction Temperature	TJ	+150	°C
Storage Temperature Range	T <sub>stg</sub>	-65 to +150	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

- 1. DPAK Junction-to-Ambient Thermal Resistance is for vertical mounting. Refer to Figure 25 for board mounted Thermal Resistance.
- 2. SOP-8 Junction-to-Ambient Thermal Resistance is for minimum recommended pad size. Refer to Figure 24 for Thermal Resistance variation versus pad size.
- 3. D<sup>2</sup>PAK Junction-to-Ambient Thermal Resistance is for vertical mounting. Refer to Figure 26 for board mounted Thermal Resistance.
- 4. NCV rated devices are subjected to and meet the AECQ-100 quality standards.

**ELECTRICAL CHARACTERISTICS** ( $V_{in} = 14 \text{ V}$ ,  $I_O = 10 \text{ mA}$ ,  $C_O = 100 \text{ }\mu\text{F}$ ,  $C_{O(ESR)} = 0.3 \Omega$ ,  $T_A = 25^{\circ}\text{C}$  [Note 5])

		LM2931-5.0/NCV2931-5.0		LM2931A	-5.0/NCV2	931A-5.0		
Characteristic	Symbol	Min	Тур	Max	Min	Тур	Max	Unit
FIXED OUTPUT		•	•	-	•	•		
Output Voltage	Vo							V
V <sub>in</sub> = 14 V, I <sub>O</sub> = 10 mA, T <sub>A</sub> = 25°C		4.75	5.0	5.25	4.81	5.0	5.19	
$V_{in}$ = 6.0 V to 26 V, $I_O \le$ 100 mA, $T_A = -40^{\circ}$ to +125°C		4.50	-	5.50	4.75	-	5.25	
Line Regulation	Reg <sub>line</sub>							mV
V <sub>in</sub> = 9.0 V to 16 V		-	2.0	10	-	2.0	10	
V <sub>in</sub> = 6.0 V to 26 V		_	4.0	30	-	4.0	30	
Load Regulation (I <sub>O</sub> = 5.0 mA to 100 mA)	Reg <sub>load</sub>	_	14	50	-	14	50	mV
Output Impedance	Z <sub>O</sub>							mΩ
$I_{O}$ = 10 mA, $\Delta I_{O}$ = 1.0 mA, f = 100 Hz to 10 kHz		-	200	=	_	200	-	
Bias Current	Ι <sub>Β</sub>							mA
V <sub>in</sub> = 14 V, I <sub>O</sub> = 100 mA, T <sub>A</sub> = 25°C		_	5.8	30	-	5.8	30	
$V_{in}$ = 6.0 V to 26 V, $I_O$ = 10 mA, $T_A$ = $-40^{\circ}$ to $+125^{\circ}C$		-	0.4	1.0	_	0.4	1.0	
Output Noise Voltage (f = 10 Hz to 100 kHz)	V <sub>n</sub>	_	700	-	-	700	-	μVrms
Long Term Stability	S	_	20	_	-	20	_	mV/kHR
Ripple Rejection (f = 120 Hz)	RR	60	90	_	60	90	_	dB
Dropout Voltage	$V_I$ – $V_O$							V
I <sub>O</sub> = 10 mA		-	0.015	0.2	-	0.015	0.2	
I <sub>O</sub> = 100 mA		-	0.16	0.6	-	0.16	0.6	
Over-Voltage Shutdown Threshold	V <sub>th(OV)</sub>	26	29.5	40	26	29.5	40	V
Output Voltage with Reverse Polarity Input (V <sub>in</sub> = -15 V)	-V <sub>O</sub>	-0.3	0	-	-0.3	0	-	V

<sup>5.</sup> Low duty cycle pulse techniques are used during test to maintain junction temperature as close to ambient as possible.6. NCV devices are qualified for automotive use.

 $\textbf{ELECTRICAL CHARACTERISTICS} \ (V_{in} = 14 \ V, \ I_O = 10 \ mA, \ C_O = 100 \ \mu F, \ C_{O(ESR)} = 0.3 \ \Omega, \ T_A = 25^{\circ}C \ [Note \ 7])$ 

		LM29	31C/NCV	2931C	LM2931AC/NCV2931AC			
Characteristic	Symbol	Min	Тур	Max	Min	Тур	Max	Unit
ADJUSTABLE OUTPUT								•
Reference Voltage (Note 8, Figure 18) $I_O = 10$ mA, $T_A = 25^{\circ}$ C $I_O \le 100$ mA, $T_A = -40$ to $+125^{\circ}$ C	V <sub>ref</sub>	1.14 1.08	1.20	1.26 1.32	1.17 1.15	1.20	1.23 1.25	V
Output Voltage Range	V <sub>O range</sub>	3.0 to 24	2.7 to 29.5	-	3.0 to 24	2.7 to 29.5	-	V
Line Regulation (V <sub>in</sub> = V <sub>O</sub> + 0.6 V to 26 V)	Reg <sub>line</sub>	_	0.2	1.5	-	0.2	1.5	mV/V
Load Regulation (I <sub>O</sub> = 5.0 mA to 100 mA)	Reg <sub>load</sub>	_	0.3	1.0	-	0.3	1.0	%/V
Output Impedance $I_O = 10$ mA, $\Delta I_O = 1.0$ mA, $f = 10$ Hz to 10 kHz	Z <sub>O</sub>	_	40	-	_	40	-	mΩ/V
Bias Current $I_O = 100 \text{ mA}$ $I_O = 10 \text{ mA}$ Output Inhibited ( $V_{th(OI)} = 2.5 \text{ V}$ )	I <sub>B</sub>		6.0 0.4 0.2	- 1.0 1.0	- - -	6.0 0.4 0.2	- 1.0 1.0	mA
Adjustment Pin Current	I <sub>Adj</sub>	_	0.2	-	-	0.2	-	μΑ
Output Noise Voltage (f = 10 Hz to 100 kHz)	V <sub>n</sub>	-	140	-	-	140	-	μVrms/V
Long-Term Stability	S	-	0.4	-	-	0.4	-	%/kHR
Ripple Rejection (f = 120 Hz)	RR	0.10	0.003	-	0.10	0.003	-	%/V
Dropout Voltage $I_O = 10 \text{ mA}$ $I_O = 100 \text{ mA}$	V <sub>I</sub> –V <sub>O</sub>	- -	0.015 0.16	0.2 0.6	_ _	0.015 0.16	0.2 0.6	V
Over-Voltage Shutdown Threshold	$V_{th(OV)}$	26	29.5	40	26	29.5	40	V
Output Voltage with Reverse Polarity Input $(V_{in} = -15 \text{ V})$	-V <sub>O</sub>	-0.3	0	-	-0.3	0	-	V
Output Inhibit Threshold Voltages  Output "On": $T_A = 25^{\circ}C$ $T_A = -40^{\circ}$ to +125°C  Output "Off": $T_A = 25^{\circ}C$ $T_A = -40^{\circ}$ to +125°C	V <sub>th(OI)</sub>	- 2.50 3.25	2.15 - 2.26 -	1.90 1.20 - -	- 2.50 3.25	2.15 - 2.26 -	1.90 1.20 - -	V
Output Inhibit Threshold Current (V <sub>th(OI)</sub> = 2.5 V)	I <sub>th(OI)</sub>	_	30	50	-	30	50	μΑ

<sup>7.</sup> Low duty cycle pulse techniques are used during test to maintain junction temperature as close to ambient as possible.
8. The reference voltage on the adjustable device is measured from the output to the adjust pin across R<sub>1</sub>.

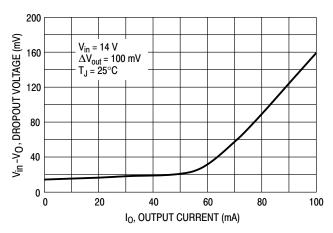


Figure 1. Dropout Voltage versus Output Current

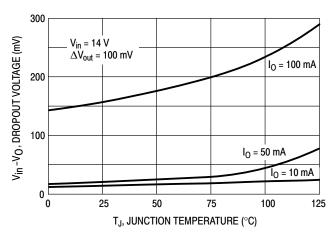


Figure 2. Dropout Voltage versus Junction Temperature

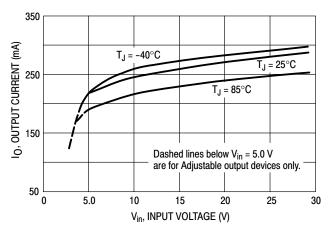


Figure 3. Peak Output Current versus Input Voltage

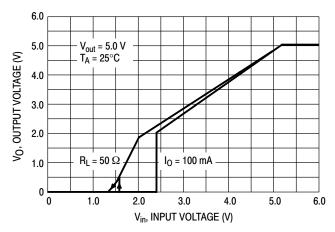


Figure 4. Output Voltage versus Input Voltage

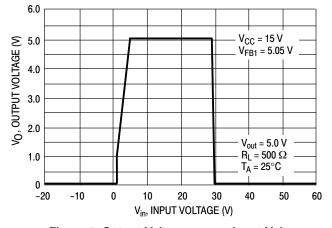


Figure 5. Output Voltage versus Input Voltage

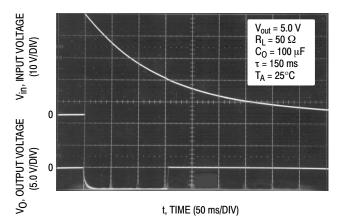


Figure 6. Load Dump Characteristics

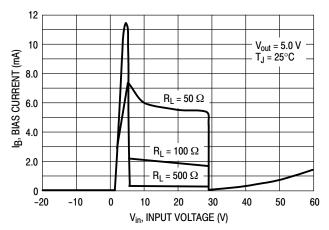


Figure 7. Bias Current versus Input Voltage

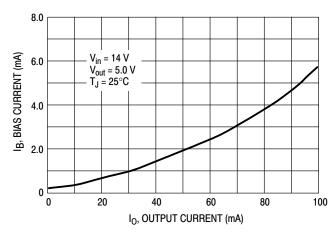


Figure 8. Bias Current versus Output Current

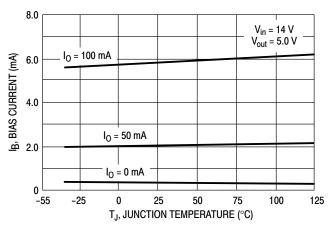


Figure 9. Bias Current versus Junction Temperature

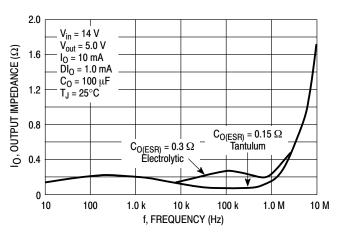


Figure 10. Output Impedance versus Frequency

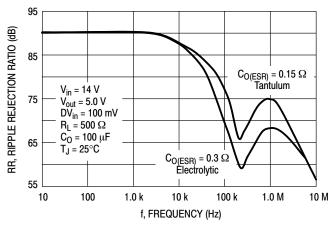


Figure 11. Ripple Rejection versus Frequency

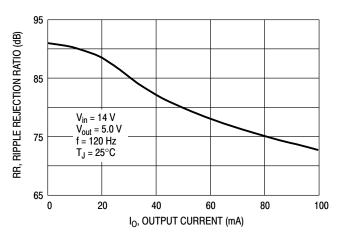


Figure 12. Ripple Rejection versus Output Current

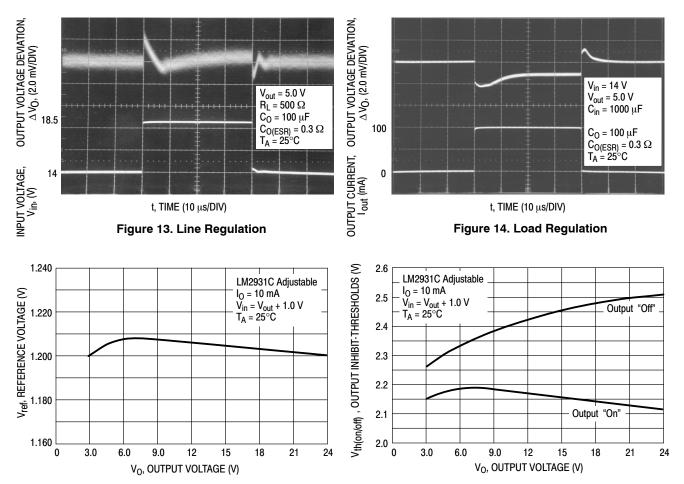


Figure 15. Reference Voltage versus Output Voltage

Figure 16. Output Inhibit-Thresholds versus Output Voltage

#### **APPLICATIONS INFORMATION**

The LM2931 series regulators are designed with many protection features making them essentially blow-out proof. These features include internal current limiting, thermal shutdown, overvoltage and reverse polarity input protection, and the capability to withstand temporary power-up with mirror-image insertion. Typical application circuits for the fixed and adjustable output device are shown in Figures 17 and 18.

The input bypass capacitor  $C_{in}$  is recommended if the regulator is located an appreciable distance ( $\geq 4''$ ) from the supply input filter. This will reduce the circuit's sensitivity to the input line impedance at high frequencies.

This regulator series is not internally compensated and thus requires an external output capacitor for stability. The capacitance value required is dependent upon the load current, output voltage for the adjustable regulator, and the type of capacitor selected. The least stable condition is encountered at maximum load current and minimum output voltage. Figure 22 shows that for operation in the "Stable" region, under the conditions specified, the magnitude of the output capacitor impedance  $|Z_O|$  must not exceed 0.4  $\Omega$ . This

limit must be observed over the entire operating temperature range of the regulator circuit.

With economical electrolytic capacitors, cold temperature operation can pose a serious stability problem. As the electrolyte freezes, around  $-30^{\circ}\mathrm{C}$ , the capacitance will decrease and the equivalent series resistance (ESR) will increase drastically, causing the circuit to oscillate. Quality electrolytic capacitors with extended temperature ranges of  $-40^{\circ}$  to  $+85^{\circ}\mathrm{C}$  and  $-55^{\circ}$  to  $+105^{\circ}\mathrm{C}$  are readily available. Solid tantalum capacitors may be a better choice if small size is a requirement, however, the maximum  $\left| \mathbf{Z}_{O} \right|$  limit over temperature must be observed.

Note that in the stable region, the output noise voltage is linearly proportional to  $\left| Z_O \right|$ . In effect,  $C_O$  dictates the high frequency roll–off point of the circuit. Operation in the area titled "Marginally Stable" will cause the output of the regulator to exhibit random bursts of oscillation that decay in an under–damped fashion. Continuous oscillation occurs when operating in the area titled "Unstable". It is suggested that oven testing of the entire circuit be performed with maximum load, minimum input voltage, and minimum ambient temperature.

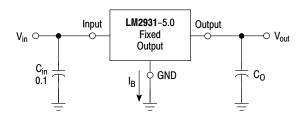
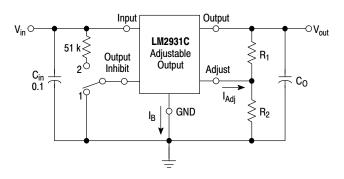


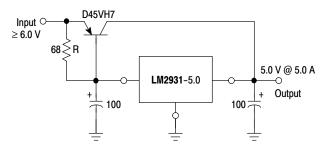
Figure 17. Fixed Output Regulator



Switch Position 1 = Output "On", 2 = Output "Off"

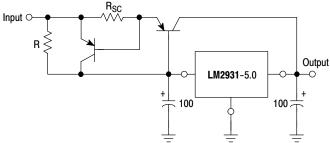
$$V_{out} = V_{ref} \left( 1 + \frac{R_2}{R_1} \right) + I_{Adj} R_2$$
  $22.5 k \ge \frac{R_1 R_2}{R_1 + R_2}$ 

Figure 18. Adjustable Output Regulator



The LM2931 series can be current boosted with a PNP transistor. The D45VH7, on a heatsink, will provide an output current of 5.0 A with an input to output voltage differential of approximately 1.0 V. Resistor R in conjunction with the  $V_{BE}$  of the PNP determines when the pass transistor begins conducting. This circuit is not short circuit proof.

Figure 19. (5.0 A) Low Differential Voltage Regulator



The circuit of Figure 19 can be modified to provide supply protection against short circuits by adding the current sense resistor  $R_{SC}$  and an additional PNP transistor. The current sensing PNP must be capable of handling the short circuit current of the LM2931. Safe operating area of both transistors must be considered under worst case conditions.

Figure 20. Current Boost Regulator with Short Circuit Projection

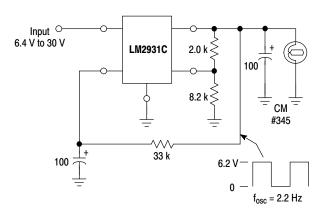
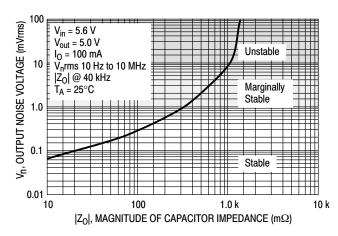


Figure 21. Constant Intensity Lamp Flasher



 $10~\mu\text{F}$ 22 μF 0.50 Unstable **47** μF 100 μΕ 0.40 ESR (Ohms) 0.30 Stable 0.20 Note - Optimum stability uses a 22  $\mu$ F 0.10 output capacitor. Output capacitor values below 10 µF are not recommended. 0.00 10 20 30 40 50 60 70 80 90 100 0 OUTPUT CURRENT (mA)

Figure 22. Output Noise Voltage vs.
Output Capacitor Impedance

Figure 23. Output Capacitor ESR Stability vs.
Output Load Current

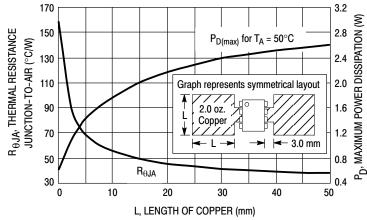


Figure 24. SOP-8 Thermal Resistance and Maximum Power Dissipation versus P.C.B. Copper Length

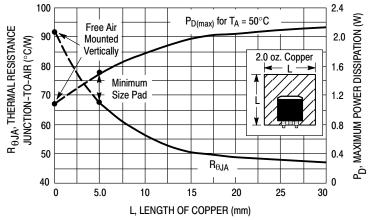


Figure 25. DPAK Thermal Resistance and Maximum Power Dissipation versus P.C.B. Copper Length

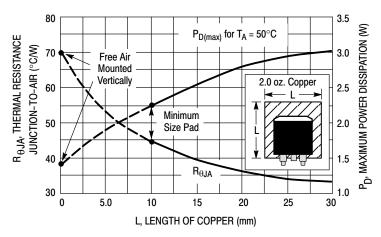


Figure 26. 3-Pin and 5-Pin D<sup>2</sup>PAK
Thermal Resistance and Maximum Power
Dissipation versus P.C.B. Copper Length

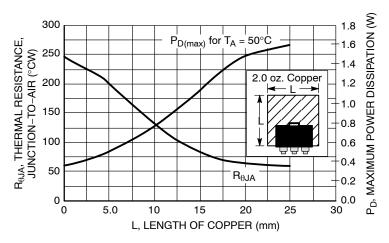


Figure 27. SOT-223 Thermal Resistance and Maximum Power Dissipation vs. P.C.B. Copper Length

#### **DEFINITIONS**

**Dropout Voltage** – The input/output voltage differential at which the regulator output no longer maintains regulation against further reductions in input voltage. Measured when the output decreases 100 mV from nominal value at 14 V input, dropout voltage is affected by junction temperature and load current.

**Line Regulation** – The change in output voltage for a change in the input voltage. The measurement is made under conditions of low dissipation or by using pulse techniques such that the average chip temperature is not significantly affected.

**Load Regulation** – The change in output voltage for a change in load current at constant chip temperature.

**Maximum Power Dissipation** – The maximum total device dissipation for which the regulator will operate within specifications.

**Bias Current** – That part of the input current that is not delivered to the load.

**Output Noise Voltage** – The rms AC voltage at the output, with constant load and no input ripple, measured over a specified frequency range.

**Long-Term Stability** – Output voltage stability under accelerated life test conditions with the maximum rated voltage listed in the devices electrical characteristics and maximum power dissipation.

#### **ORDERING INFORMATION**

	Ou	tput		
Device	Voltage	Tolerance	Package	Shipping <sup>†</sup>
LM2931AD-5.0G	5.0 V	±3.8%	SOIC-8 (Pb-Free)	98 Units / Rail
LM2931AD-5.0R2G	5.0 V	±3.8%	SOIC-8 (Pb-Free)	2500 / Tape & Reel
LM2931ADT-5.0RKG	5.0 V	±3.8%	DPAK (Pb-Free)	2500 / VacPk
LM2931AD2T-5R4G	5.0 V	±3.8%	D <sup>2</sup> PAK (Pb-Free)	800 / VacPk Reel
LM2931AT-5.0G	5.0 V	±3.8%	TO-220 (Pb-Free)	50 Units / Rail
LM2931AZ-5.0G	5.0 V	±3.8%	TO-92 (Pb-Free)	2000 / Inner Bag
LM2931AZ-5.0RAG	5.0 V	±3.8%	TO-92 (Pb-Free)	2000 / Tape & Reel
LM2931AZ-5.0RPG	5.0 V	±3.8%	TO-92 (Pb-Free)	2000 / Ammo Pack
LM2931D-5.0R2G	5.0 V	±5.0%	SOIC-8 (Pb-Free)	2500 / Tape & Reel
LM2931D2T-5.0R4G	5.0 V	±5.0%	D <sup>2</sup> PAK (Pb-Free)	800 / VacPk Reel
LM2931DT-5.0G	5.0 V	±5.0%	DPAK (Pb-Free)	75 Units / Rail
LM2931T-5.0G	5.0 V	±5.0%	TO-220 (Pb-Free)	50 Units / Rail
LM2931Z-5.0G	5.0 V	±5.0%	TO-92 (Pb-Free)	2000 / Inner Bag
LM2931Z-5.0RAG	5.0 V	±5.0%	TO-92 (Pb-Free)	2000 / Tape & Reel
LM2931Z-5.0RPG	5.0 V	±5.0%	TO-92 (Pb-Free)	2000 / Ammo Pack
LM2931CDG	Adjustable	±5.0%	SOIC-8 (Pb-Free)	98 Units / Rail
LM2931CDR2G	Adjustable	±5.0%	SOIC-8 (Pb-Free)	2500 / Tape & Reel
LM2931ACDR2G	Adjustable	±2.0%	SOIC-8 (Pb-Free)	2500 / Tape & Reel
LM2931ACD2TR4G	Adjustable	±2.0%	D <sup>2</sup> PAK (Pb-Free)	800 / VacPk Reel
NCV2931ACDR2G*	Adjustable	±2.5%	SOIC-8 (Pb-Free)	2500 / Tape & Reel
NCV2931AD-5.0R2G*	5.0 V	±3.8%	SOIC-8 (Pb-Free)	2500 / Tape & Reel
NCV2931AST-5.0T3G*	5.0 V	±3.8%	SOT-223 (Pb-Free)	4000 / Tape & Reel
NCV2931AZ-5.0G*	5.0 V	±3.8%	TO-92 (Pb-Free)	2000 / Inner Bag

<sup>†</sup>For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Spe-

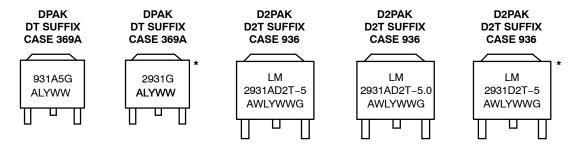
cifications Brochure, BRD8011/D.
\*NCV2931: T<sub>low</sub> = -40°C, T<sub>high</sub> = +125°C. Guaranteed by design. NCV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q100 Qualified and PPAP Capable.

#### **ORDERING INFORMATION** (continued)

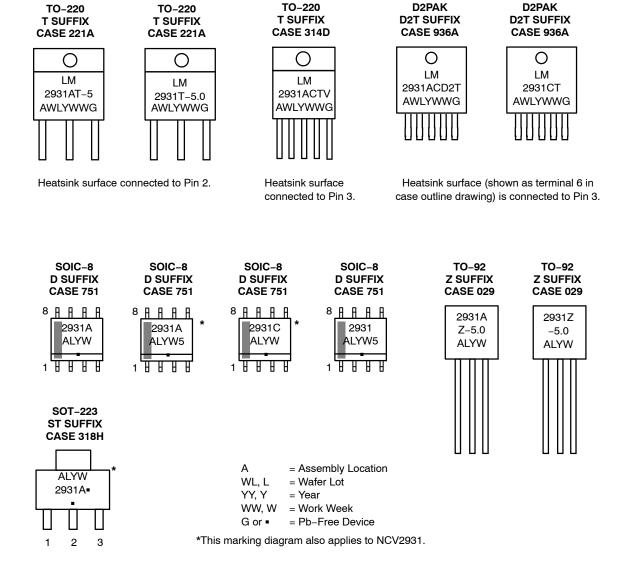
	Out	tput		
Device	Voltage	Tolerance	Package	Shipping <sup>†</sup>
NCV2931AZ-5.0RAG*	5.0 V	±3.8%	TO-92 (Pb-Free)	2000 / Tape & Reel
NCV2931CDR2G*	Adjustable	±5.0%	SOIC-8 (Pb-Free)	2500 / Tape & Reel
NCV2931D-5.0R2G*	5.0 V	±5.0%	SOIC-8 (Pb-Free)	2500 / Tape & Reel
NCV2931ADT5.0RKG*	5.0 V	±3.8%	DPAK (Pb-Free)	2500 / Tape & Reel
NCV2931DT-5.0RKG*	5.0 V	±5.0%	DPAK (Pb-Free)	2500 / Tape & Reel
NCV2931ACD2TR4G*	Adjustable	±2.5%	D <sup>2</sup> PAK (Pb-Free)	800 / VacPk Reel
NCV2931D2T5.0R4G*	5.0 V	±5.0%	D <sup>2</sup> PAK (Pb-Free)	800 / VacPk Reel

<sup>†</sup>For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.
\*NCV2931: T<sub>low</sub> = -40°C, T<sub>high</sub> = +125°C. Guaranteed by design. NCV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q100 Qualified and PPAP Capable.

#### **MARKING DIAGRAMS**



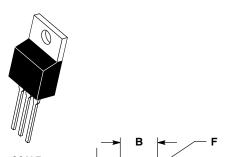
Heatsink surface (shown as terminal 4 in case outline drawing) is connected to Pin 2.



### **MECHANICAL CASE OUTLINE PACKAGE DIMENSIONS**

ON Semiconductor®





TO-220, SINGLE GAUGE CASE 221AB-01 **ISSUE A** 

**DATE 16 NOV 2010** 

- NOTES:

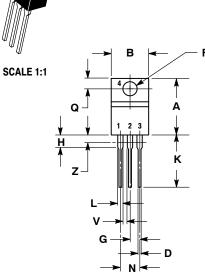
  1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.

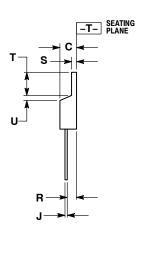
  2. CONTROLLING DIMENSION: INCHES.

  3. DIMENSION 2 DEFINES A ZONE WHERE ALL BODY AND LEAD IRREGULARTIES ARE ALLOWED.

  4. PRODUCT SHIPPED PRIOR TO 2008 HAD DIMENSIONS S = 0.045 0.055 INCHES (1.143 1.397 MM)

	INCHES		MILLIN	IETERS
DIM	MIN	MAX	MIN	MAX
Α	0.570	0.620	14.48	15.75
В	0.380	0.405	9.66	10.28
С	0.160	0.190	4.07	4.82
D	0.025	0.035	0.64	0.88
F	0.142	0.147	3.61	3.73
G	0.095	0.105	2.42	2.66
Н	0.110	0.155	2.80	3.93
J	0.018	0.025	0.46	0.64
K	0.500	0.562	12.70	14.27
L	0.045	0.060	1.15	1.52
N	0.190	0.210	4.83	5.33
Q	0.100	0.120	2.54	3.04
R	0.080	0.110	2.04	2.79
S	0.020	0.024	0.508	0.61
T	0.235	0.255	5.97	6.47
U	0.000	0.050	0.00	1.27
٧	0.045		1.15	
Z		0.080		2.04



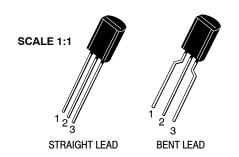


STYLE 1:		STYLE 2:		STYLE 3:	
PIN 1.	BASE	PIN 1.	BASE	PIN 1.	CATHODE
2.	COLLECTOR	2.	EMITTER	2.	ANODE
3.	EMITTER	3.	COLLECTOR	3.	GATE
4.	COLLECTOR	4.	EMITTER	4.	ANODE
STYLE 5:		STYLE 6:		STYLE 7:	
PIN 1.	GATE	PIN 1.	ANODE	PIN 1.	CATHODE
2.	DRAIN	2.	CATHODE	2.	ANODE
3.	SOURCE	3.	ANODE	3.	CATHODE
4.	DRAIN	4.	CATHODE	4.	ANODE
STYLE 9:		STYLE 10:		STYLE 11:	
PIN 1.	GATE	PIN 1.	GATE	PIN 1.	DRAIN
2.	COLLECTOR	2.	SOURCE	2.	SOURCE
3.	EMITTER	3.	DRAIN	3.	GATE
4.	COLLECTOR	4.	SOURCE	4.	SOURCE

3.	MAIN TERMINAL 1 MAIN TERMINAL 2 GATE MAIN TERMINAL 2
2. 3.	CATHODE ANODE EXTERNAL TRIP/DELAY ANODE

DOCUMENT NUMBER:	98AON23085D	Electronic versions are uncontrolled except when accessed directly from the Document Repos Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.	
DESCRIPTION:	TO-220, SINGLE GAUGE		PAGE 1 OF 1

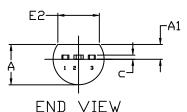
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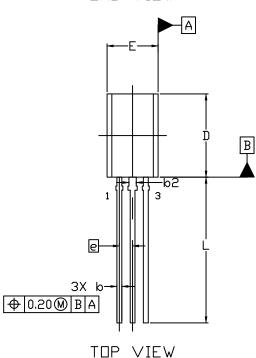


TO-92 (TO-226) 1 WATT CASE 29-10 ISSUE D

**DATE 05 MAR 2021** 

#### STRAIGHT LEAD





#### NOTES:

- DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 2009.
- 2. CONTROLLING DIMENSION: MILLIMETERS
- 3. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH OR GATE PROTRUSIONS.
- 4. DIMENSION 6 AND 62 DOES NOT INCLUDE DAMBAR PROTRUSION. LEAD WIDTH INCLUDING PROTRUSION SHALL NOT EXCEED 0.20. DIMENSION 62 LOCATED ABOVE THE DAMBAR PORTION OF MIDDLE LEAD.

	MILLIMETERS			
DIM	MIN.	N□M.	MAX.	
Δ	3.75	3.90	4.05	
A1	1.28	1.43	1.58	
Ø	0.38	0.465	0.55	
ρQ	0.62	0.70	0.78	
C	0.35	0.40	0.45	
D	7.85	8.00	8.15	
E	4.75	4.90	5.05	
E2	3.90			
е	1.27 BSC			
L	13.80	14.00	14.20	

#### STYLES AND MARKING ON PAGE 3

DOCUMENT NUMBER:	98AON52857E	Electronic versions are uncontrolled except when accessed directly from the Document Reposit Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.	
DESCRIPTION:	TO-92 (TO-226) 1 WATT		PAGE 1 OF 3

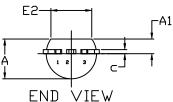
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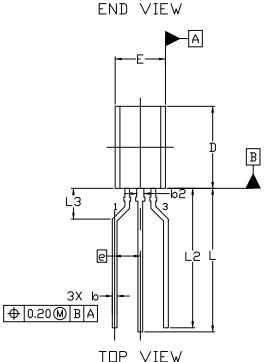


TO-92 (TO-226) 1 WATT CASE 29-10 ISSUE D

**DATE 05 MAR 2021** 

#### FORMED LEAD





#### NOTES:

- DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 2009.
- 2. CONTROLLING DIMENSION: MILLIMETERS
- 3. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH OR GATE PROTRUSIONS.
- 4. DIMENSION 6 AND 62 DOES NOT INCLUDE DAMBAR PROTRUSION. LEAD WIDTH INCLUDING PROTRUSION SHALL NOT EXCEED 0.20. DIMENSION 62 LOCATED ABOVE THE DAMBAR PORTION OF MIDDLE LEAD.

	MILLIMETERS				
DIM	MIN.	N□M.	MAX.		
Α	3.75	3.90	4.05		
A1	1.28	1.43	1.58		
b	0.38	0.465	0.55		
b2	0.62	0.70	0.78		
С	0.35	0.40	0.45		
D	7.85	8.00	8.15		
Е	4.75	4.90	5.05		
E2	3.90				
O.		2.50 BSC			
L	13.80	14.00	14.20		
L2	13.20	13.60	14.00		
L3	3.00 REF				

#### **STYLES AND MARKING ON PAGE 3**

DOCUMENT NUMBER:	98AON52857E	Electronic versions are uncontrolled except when accessed directly from the Document Repos Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.	
DESCRIPTION:	TO-92 (TO-226) 1 WATT		PAGE 2 OF 3

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#### TO-92 (TO-226) 1 WATT

CASE 29-10 ISSUE D

#### **DATE 05 MAR 2021**

2.	EMITTER BASE COLLECTOR	STYLE 2: PIN 1. 2. 3.	BASE EMITTER COLLECTOR	STYLE 3: PIN 1. 2. 3.	ANODE ANODE CATHODE	PIN 1. 2.	CATHODE CATHODE ANODE	STYLE 5: PIN 1. 2. 3.	
	GATE	PIN 1.	SOURCE DRAIN	PIN 1. 2.	DRAIN	2.	BASE 1 EMITTER BASE 2		CATHODE GATE ANODE
2.	CATHODE & ANODE	2.	MAIN TERMINAL 1 GATE MAIN TERMINAL 2	2.	ANODE 1 GATE CATHODE 2		EMITTER COLLECTOR BASE	STYLE 15: PIN 1. 2. 3.	ANODE 1
2.	ANODE	DINI 1	COLLECTOR BASE EMITTER	PIN 1	ANODE	PIN 1. 2.	GATE ANODE CATHODE	2.	NOT CONNECTED CATHODE ANODE
2.		PIN 1. 2.		PIN 1. 2.	GATE	PIN 1. 2.	EMITTER COLLECTOR/ANODE CATHODE	PIN 1. 2.	MT 1
	V <sub>CC</sub>		MT	PIN 1. 2.		PIN 1. 2.	NOT CONNECTED ANODE CATHODE	PIN 1. 2.	
		STYLE 32: PIN 1. 2. 3.	BASE COLLECTOR EMITTER	STYLE 33: PIN 1. 2. 3.	RETURN	PIN 1. 2.	INPUT GROUND LOGIC		

# GENERIC MARKING DIAGRAM\*



XXXX = Specific Device Code

A = Assembly Location

L = Wafer Lot Y = Year

W = Work Week

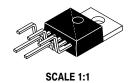
= Pb-Free Package

(Note: Microdot may be in either location)

\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "•", may or may not be present. Some products may not follow the Generic Marking.

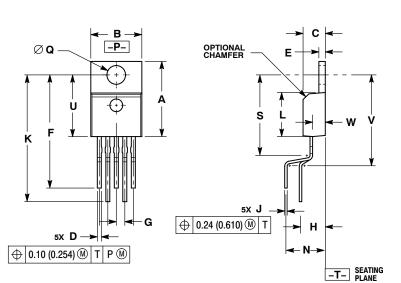
DOCUMENT NUMBER:	98AON52857E	Electronic versions are uncontrolled except when accessed directly from the Document Repos Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.	
DESCRIPTION:	TO-92 (TO-226) 1 WATT		PAGE 3 OF 3

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#### **TO-220 5 LEAD OFFSET CASE 314B-05 ISSUE L**

DATE 01/07/1994



- NOTES:
  1 DIMENSIONING AND TOLERANCING PER ANSI
  Y14.5M, 1982.
  2. CONTROLLING DIMENSION: INCH.
  3. DIMENSION D DOES NOT INCLUDE
  INTERCONNECT BAR (DAMBAR) PROTRUSION.
  DIMENSION D INCLUDING PROTRUSION SHALL NOT EXCEED 0.043 (1.092) MAXIMUM.

	INCHES		MILLIMETERS		
DIM	MIN	MAX	MIN	MAX	
Α	0.572	0.613	14.529	15.570	
В	0.390	0.415	9.906	10.541	
С	0.170	0.180	4.318	4.572	
D	0.025	0.038	0.635	0.965	
Е	0.048	0.055	1.219	1.397	
F	0.850	0.935	21.590	23.749	
G	0.067	BSC	1.702 BSC		
Н	0.166	BSC	4.216 BSC		
J	0.015	0.025	0.381	0.635	
K	0.900	1.100	22.860	27.940	
L	0.320	0.365	8.128	9.271	
N	0.320	BSC	8.128 BSC		
Q	0.140	0.153	3.556	3.886	
S		0.620		15.748	
U	0.468	0.505	11.888	12.827	
٧		0.735		18.669	
W	0.090	0.110	2.286	2.794	

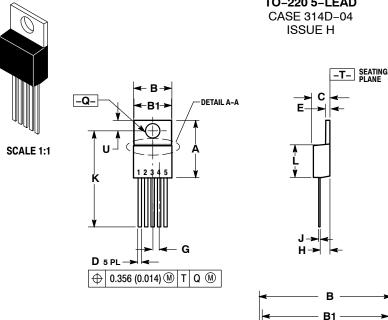
STYLE 1 THRU 4: CANCELLED

- STYLE 5: PIN 1. GATE
  - 2. MIRROR 3. DRAIN

  - 4. KELVIN 5. SOURCE

DOCUMENT NUMBER:	98ASB42218B	Electronic versions are uncontrolled except when accessed directly from the Document Rep Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.	
DESCRIPTION	TO-220 5 LEAD OFFSET	•	PAGE 1 OF 1

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TO-220 5-LEAD

**DATE 29 JAN 2010** 

#### NOTES:

- DIMENSIONING AND TOLERANCING PER ANSI
  Y14.5M. 1982.
- Y14.5M, 1982.

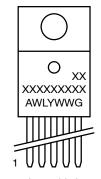
  2. CONTROLLING DIMENSION: INCH.

  3. DIMENSION D DOES NOT INCLUDE
  INTERCONNECT BAR (DAMBAR) PROTRUSION.
  DIMENSION D INCLUDING PROTRUSION SHALL NOT EXCEED 10.92 (0.043) MAXIMUM.

	INC	HES	MILLIN	IETERS	
DIM	MIN	MAX	MIN	MAX	
Α	0.572	0.613	14.529	15.570	
В	0.390	0.415	9.906	10.541	
B1	0.375	0.415	9.525	10.541	
С	0.170	0.180	4.318	4.572	
D	0.025	0.038	0.635	0.965	
E	0.048	0.055	1.219	1.397	
G	0.067	BSC	1.702 BSC		
Н	0.087	0.112	2.210	2.845	
J	0.015	0.025	0.381	0.635	
K	0.977	1.045	24.810	26.543	
L	0.320	0.365	8.128	9.271	
Q	0.140	0.153	3.556	3.886	
U	0.105	0.117	2.667	2.972	

STYLE 1 THRU 4: 1. OBSOLETE

#### **GENERIC MARKING DIAGRAM\***



= Assembly Location

WL = Wafer Lot

= Year

WW = Work Week

G = Pb-Free Package

\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot " ■", may or may not be present.

DOCUMENT NUMBER:	98ASB42220B	Electronic versions are uncontrolled except when accessed directly from the Document Repositor Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.	
DESCRIPTION:	TO-220 5-LEAD		PAGE 1 OF 1

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SCALE 2:1



A

В

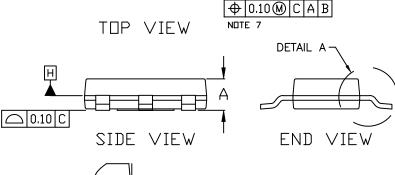
**DATE 13 MAY 2020** 

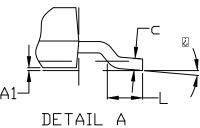
#### NOTES

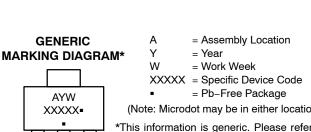
- DIMENSIONING AND TOLERANCING PER ASME
- DIMENSIDNING AND TOLERANCING PER ASME
  Y14.5M, 2009.
  CONTROLLING DIMENSION: MILLIMETERS
  DIMENSIONS D & E1 ARE DETERMINED AT DATUM
  H. DIMENSIONS DO NOT INCLUDE MOLD FLASH,
  PROTRUSIONS DR GATE BURRS. SHALL NOT
  EXCEED 0.23mm PER SIDE.
  LEAD DIMENSIONS & AND &1 DO NOT INCLUDE
  DAMBAR PROTRUSION. ALLOWABLE DAMBBAR
  PROTRUSION IS 0.08mm PER SIDE.
  DATUMS A AND B ARE DETERMINED AT DATUM H.
  A1 IS DEFINED AS THE VERTICAL DISTANCE
  FROM THE SEATING PLANE TO THE LOWEST
  POINT OF THE PACKAGE BODY.
  POSITIONAL TOLERANCE APPLIES TO DIMENSIONS
  & AND &1.

- b AND b1.

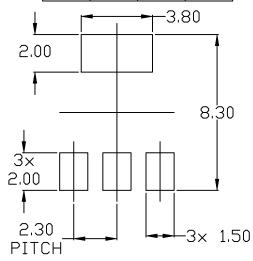
	MILLIMETERS			
DIM	MIN.	N□M.	MAX.	
Α			1.80	
A1	0.02	0.06	0.11	
b	0.60	0.74	0.88	
b1	2.90	3.00	3.10	
c	0.24		0.35	
D	6.30	6.50	6.70	
E	6.70	7.00	7.30	
E1	3.30	3.50	3.70	
е	2.30 BSC			
L	0.25			
Ŀ	0*		10°	







(Note: Microdot may be in either location) \*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "•", may or may not be present. Some products may not follow the Generic Marking.



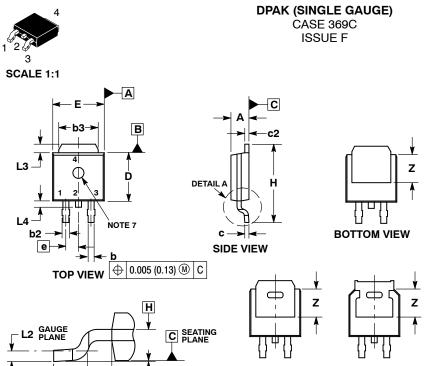
#### RECOMMENDED MOUNTING FOOTPRINT

For additional information on our Pb-Free strategy and soldering details, please download the IN Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

DOCUMENT NUMBER:	98ASH70634A  Electronic versions are uncontrolled except when accessed alrectly from the Document Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.			
DESCRIPTION:	SOT-223		PAGE 1 OF 1	

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**DATE 21 JUL 2015** 



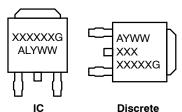
#### NOTES:

- DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
   CONTROLLING DIMENSION: INCHES.
- 3. THERMAL PAD CONTOUR OPTIONAL WITHIN DI-
- MENSIONS b3, L3 and Z.
  4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR BURRS. MOLD FLASH, PROTRUSIONS, OR GATE BURRS SHALL NOT EXCEED 0.006 INCHES PER SIDE.
  5. DIMENSIONS D AND E ARE DETERMINED AT THE
- OUTERMOST EXTREMES OF THE PLASTIC BODY.

  6. DATUMS A AND B ARE DETERMINED AT DATUM
- 7. OPTIONAL MOLD FEATURE.

	INC	HES	MILLIMETERS		
DIM	MIN	MAX	MIN	MAX	
Α	0.086	0.094	2.18	2.38	
A1	0.000	0.005	0.00	0.13	
b	0.025	0.035	0.63	0.89	
b2	0.028	0.045	0.72	1.14	
b3	0.180	0.215	4.57	5.46	
С	0.018	0.024	0.46	0.61	
c2	0.018	0.024	0.46	0.61	
D	0.235	0.245	5.97	6.22	
E	0.250	0.265	6.35	6.73	
е	0.090	BSC	2.29 BSC		
Н	0.370	0.410	9.40	10.41	
L	0.055	0.070	1.40	1.78	
L1	0.114 REF		2.90 REF		
L2	0.020 BSC		0.51 BSC		
L3	0.035	0.050	0.89	1.27	
L4		0.040		1.01	
Z	0.155		3.93		

#### **GENERIC MARKING DIAGRAM\***



XXXXXX = Device Code

= Assembly Location Α

L = Wafer Lot Υ = Year WW = Work Week G = Pb-Free Package

\*This information is generic. Please refer to device data sheet for actual part marking.

# **SOLDERING FOOTPRINT\***

STYLE 8:

STYLE 3:

PIN 1. N/C 2. CATHODE

3. ANODE 4. CATHODE

PIN 1. ANODE 2. CATHODE

3. ANODE

4. CATHODE

STYLE 9:

PIN 1. ANODE 2. CATHODE

Α1

STYLE 2:

PIN 1. GATE 2. COLLECTOR

3. EMITTER 4. COLLECTOR

PIN 1. GATE 2. DRAIN

SOURCE

4. DRAIN

**DETAIL A** ROTATED 90° CW

STYLE 7:

STYLE 1:

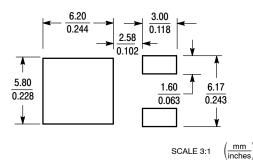
STYLE 6:

PIN 1. MT1 2. MT2

3. GATE 4. MT2

PIN 1. BASE 2. COLLECTOR 3. EMITTER

4. COLLECTOR



\*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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DESCRIPTION:	DPAK (SINGLE GAUGE)		PAGE 1 OF 1

**BOTTOM VIEW** 

ALTERNATE CONSTRUCTIONS

STYLE 5:

STYLE 10:

PIN 1. GATE 2. ANODE 3. CATHODE

4. ANODE

PIN 1. CATHODE 2. ANODE

3. CATHODE 4. ANODE

STYLE 4:

PIN 1. CATHODE 2. ANODE 3. GATE

4. ANODE

3. RESISTOR ADJUST 4. CATHODE

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SOIC-8 NB CASE 751-07 **ISSUE AK** 

**DATE 16 FEB 2011** 



- NOTES:
  1. DIMENSIONING AND TOLERANCING PER
- ANSI Y14.5M, 1982.
  CONTROLLING DIMENSION: MILLIMETER.
- DIMENSION A AND B DO NOT INCLUDE MOLD PROTRUSION.
- MAXIMUM MOLD PROTRUSION 0.15 (0.006) PER SIDE
- DIMENSION D DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.127 (0.005) TOTAL IN EXCESS OF THE D DIMENSION AT MAXIMUM MATERIAL CONDITION.
- 751-01 THRU 751-06 ARE OBSOLETE. NEW STANDARD IS 751-07.

	MILLIMETERS		INCHES		
DIM	MIN	MAX	MIN	MAX	
Α	4.80	5.00	0.189	0.197	
В	3.80	4.00	0.150	0.157	
С	1.35	1.75	0.053	0.069	
D	0.33	0.51	0.013	0.020	
G	1.27	7 BSC	0.050 BSC		
Н	0.10	0.25	0.004	0.010	
J	0.19	0.25	0.007	0.010	
K	0.40	1.27	0.016	0.050	
М	0 °	8 °	0 °	8 °	
N	0.25	0.50	0.010	0.020	
S	5.80	6.20	0.228	0.244	

#### **SOLDERING FOOTPRINT\***



<sup>\*</sup>For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

#### **GENERIC MARKING DIAGRAM\***



XXXXX = Specific Device Code = Assembly Location

= Wafer Lot = Year = Work Week

= Pb-Free Package



XXXXXX = Specific Device Code = Assembly Location Α

= Year ww = Work Week

= Pb-Free Package

\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "•", may or may not be present. Some products may not follow the Generic Marking.

#### **STYLES ON PAGE 2**

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#### SOIC-8 NB CASE 751-07 ISSUE AK

### DATE 16 FEB 2011

STYLE 3: PIN 1. DRAIN, PIE #1 CTOR, #1 CTOR, #2 CTOR, #1 CTOR, #2 CTOR, #2 CTOR, #2 CTOR, #2 CTOR, #1	2. ANODE 3. ANODE 4. ANODE 5. ANODE 6. ANODE 7. ANODE 8. COMMON CATHODE  STYLE 8: PIN 1. COLLECTOR, DIE #1 2. BASE, #1 3. BASE, #2 4. COLLECTOR, #2 5. COLLECTOR, #2 6. EMITTER, #1 Vd  STYLE 12: PIN 1. SOURCE 2. SOURCE 3. SOURCE 3. SOURCE 4. GATE 5. DRAIN 6. DRAIN 7. DRAIN 8. DRAIN 8. TYLE 16: PIN 1. EMITTER, DIE #1 2. BASE, DIE #1 3. EMITTER, DIE #1
E PIN 1. INPUT 2. EXTERNAL BY 3. THIRD STAGE 4. GROUND E 5. DRAIN 6. GATE 3 7. SECOND STAGE 8. FIRST STAGE STYLE 11: ID PIN 1. SOURCE 1 2. GATE 1 T 3. SOURCE 2 ID 4. GATE 2 ID 5. DRAIN 2 6. DRAIN 2 7. DRAIN 1 ID 8. DRAIN 1 ID	PIN 1. COLLECTOR, DIE #1 2. BASE, #1 3. BASE, #2 4. COLLECTOR, #2 5. COLLECTOR, #2 6. EMITTER, #2 7. EMITTER, #1 Vd 8. COLLECTOR, #1  STYLE 12: PIN 1. SOURCE 2. SOURCE 3. SOURCE 4. GATE 5. DRAIN 6. DRAIN 7. DRAIN 8. DRAIN 8. TYLE 16: PIN 1. EMITTER, DIE #1 2. BASE, DIE #1 3. EMITTER, DIE #2
ID PIN 1. SOURCE 1 2. GATE 1 T 3. SOURCE 2 ID 4. GATE 2 ID 5. DRAIN 2 6. DRAIN 2 7. DRAIN 1 ID 8. DRAIN 1 STYLE 15: RCE PIN 1. ANODE 1 E 2. ANODE 1 RCE 3. ANODE 1	PIN 1. SOURCE 2. SOURCE 3. SOURCE 4. GATE 5. DRAIN 6. DRAIN 7. DRAIN 8. DRAIN STYLE 16: PIN 1. EMITTER, DIE #1 2. BASE, DIE #1 3. EMITTER, DIE #2
STYLE 15:  RCE PIN 1. ANODE 1 E 2. ANODE 1 RCE 3. ANODE 1	PIN 1. EMITTER, DIE #1 2. BASE, DIE #1 3. EMITTER, DIE #2
N 7. CATHODE, CON N 8. CATHODE, CON	MMON         5. COLLECTOR, DIE #2           MMON         6. COLLECTOR, DIE #2           MMON         7. COLLECTOR, DIE #1           MMON         8. COLLECTOR, DIE #1
STYLE 19: PIN 1. SOURCE 1 E 2. GATE 1 E 3. SOURCE 2 4. GATE 2 5. DRAIN 2 6. MIRROR 2 DE 7. DRAIN 1 DE 8. MIRROR 1	STYLE 20: PIN 1. SOURCE (N) 2. GATE (N) 3. SOURCE (P) 4. GATE (P) 5. DRAIN 6. DRAIN 7. DRAIN 8. DRAIN
STYLE 23: E1 PIN 1. LINE 1 IN DN CATHODE/VCC 2. COMMON ANC DN CATHODE/VCC 3. COMMON ANC E3 4. LINE 2 IN DN ANODE/GND 5. LINE 2 OUT E4 6. COMMON ANC E5 7. COMMON ANC DN ANODE/GND 8. LINE 1 OUT	ODE/GND 2. EMITTER ODE/GND 3. COLLECTOR/ANODE
STYLE 27: PIN 1. ILIMIT 2. OVLO 3. UVLO 4. INPUT+ 5. SOURCE 6. SOURCE 6. SOURCE 7. SOURCE 8. DRAIN	STYLE 28: PIN 1. SW_TO_GND 2. DASIC_OFF 3. DASIC_SW_DET 4. GND 5. V MON 6. VBULK 7. VBULK 8. VIN
1 1	
;	STYLE 27: PIN 1. ILIMIT 2. OVLO 3. UVLO 4. INPUT+ E 5. SOURCE E 6. SOURCE E 7. SOURCE 8. DRAIN

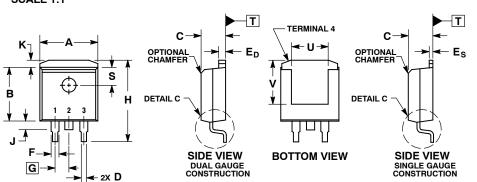
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DESCRIPTION:	SOIC-8 NB		PAGE 2 OF 2

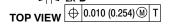
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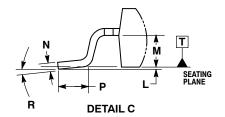


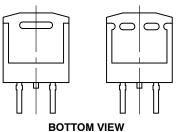
#### D<sup>2</sup>PAK CASE 936-03 ISSUE E

#### **DATE 29 SEP 2015**







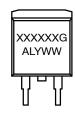


**OPTIONAL CONSTRUCTIONS** 

- DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982. CONTROLLING DIMENSION: INCHES. TAB CONTOUR OPTIONAL WITHIN DIMENSIONS
- A AND K.
  DIMENSIONS U AND V ESTABLISH A MINIMUM
- MOUNTING SURFACE FOR TERMINAL 4.
  DIMENSIONS A AND B DO NOT INCLUDE MOLD FLASH OR GATE PROTRUSIONS. MOLD FLASH AND GATE PROTRUSIONS NOT TO EXCEED 0.025 (0.635) MAXIMUM.
- SINGLE GAUGE DESIGN WILL BE SHIPPED AF-TER FPCN EXPIRATION IN OCTOBER 2011.

	INCHES		MILLIMETERS		
DIM	MIN	MAX	MIN	MAX	
Α	0.386	0.403	9.804	10.236	
В	0.356	0.368	9.042	9.347	
С	0.170	0.180	4.318	4.572	
D	0.026	0.036	0.660	0.914	
ED	0.045	0.055	1.143	1.397	
Es	0.018	0.026	0.457	0.660	
F	0.051 REF		1.295 REF		
G	0.100 BSC		2.540 BSC		
Н	0.539 0.579		13.691 14.707		
J	0.125 MAX		3.175 MAX		
K	0.050	0.050 REF		1.270 REF	
L	0.000	0.010	0.000	0.254	
M	0.088	0.102	2.235	2.591	
N	0.018	0.026	0.457	0.660	
P	0.058	0.078	1.473	1.981	
R	0°	8°	0°	8°	
S	0.116	0.116 REF		2.946 REF	
U	0.200 MIN		5.080 MIN		
V	0.250 MIN		6.350 MIN		

#### **GENERIC MARKING DIAGRAM\***



XXXXXX = Specific Device Code

= Assembly Location

= Wafer Lot 1 Υ = Year ww = Work Week G = Pb-Free Package

	ļ ,		
16.155		. ———	- 8.380 
16.155			2X 3.504

**SOLDERING FOOTPRINT\*** 

**←** 10.490 →

	ļ [			2X 3.504
2X	(1.016 →		Ī	<u> </u>
		5.080 PITCH	DIME	NSIONS: MILLI

\*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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<sup>\*</sup>This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot " ■", may or may not be present.

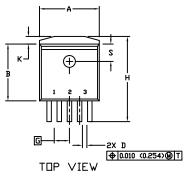
# **MECHANICAL CASE OUTLINE**

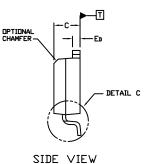


#### D<sup>2</sup>PAK 5-LEAD CASE 936A-02 **ISSUE E**

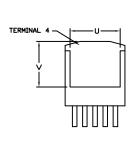
**DATE 28 JUL 2021** 

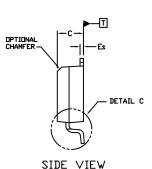






DUAL GUAGE



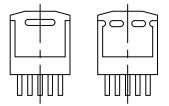


BOTTOM VIEW

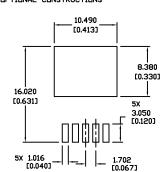
SINGLE GUAGE

SEATING

DETAIL C TIP LEADFORM ROTATED 90° CW



BOTTOM VIEW OPTIONAL CONSTRUCTIONS



#### RECOMMENDED MOUNTING FOOTPRINT \*

For additional information on our Pb-Free strategy and soldering details, please download the IN Seniconductor Soldering and Mounting Techniques Reference Manual, SILDERRM/D.

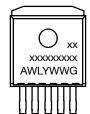
PITCH

#### NOTES

- 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
- 2. CONTROLLING DIMENSION: INCHES
- TAB CONTOUR OPTIONAL WITHIN DIMENSIONS
- DIMENSIONS U AND V ESTABLISH A MINIMUM MOUNTING SURFACE FOR TERMINAL 4.
- DIMENSIONS A AND B DO NOT INCLUDE MOLD FLASH OR GATE PROTRUSIONS. MOLD FLASH AND GATE PROTRUSIONS NOT TO EXCEED 0.025 (0.635) MAXIMUM.

	INCHES		MILLIN	IETERS
DIM	MIN.	MAX.	MIN.	MAX.
Α	0.396	0.403	9.804	10.236
В	0.356	0.368	9.042	9.347
С	0.170	0.180	4.318	4.572
D	0.026	0.036	0.660	0.914
ED	0.045	0.055	1.143	1.397
Es	0.018	0.026	0.457	0.660
G	0.067	BSC	1.702 BSC	
H	0.539	0.579	13.691	14.707
К	0.050 REF		1.270 REF	
L	0.000	0.010	0.000	0.254
М	0.088	0.102	2.235	2.591
N	0.018	0.026	0.457	0.660
Р	0.058	0.078	1.473	1.981
R	•	8.	0*	8*
S	0.116 REF		2.946 REF	
5	0.200 MIN		5.080 MIN	
<b>V</b>	0.250 MIN		6.350 MIN	

#### **GENERIC MARKING DIAGRAM\***



= Device Code XXXXXX = Assembly Location Α WL = Wafer Lot

= Year WW = Work Week G = Pb-Free Package

\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "=", may or may not be present. Some products may not follow the Generic Marking.

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5.0R2G NCV2931DT-5.0RK NCV2931DT-5.0RKG LM2931ACD LM2931ACD2TR4 LM2931ACD2TR4G

LM2931ACDG LM2931ACDR2 LM2931ACDR2G LM2931ACTV LM2931ACTVG LM2931AD2T-5.0 LM2931AD2T
5.0G LM2931AD2T-5.0R4 LM2931AD2T-5R4G LM2931AD-5.0 LM2931AD-5.0G LM2931AD-5.0R2 LM2931AD
5.0R2G LM2931ADT-5.0 LM2931ADT-5.0G LM2931ADT-5.0RK LM2931ADT-5.0RKG LM2931AT-5.0 LM2931AT
5.0G LM2931AZ-5.0 LM2931AZ-5.0G LM2931AZ-5.0RA LM2931AZ-5.0RAG LM2931AZ-5.0RP LM2931CD2T LM2931CD2TG LM2931CD2TR4 LM2931CD2TR4G LM2931CDG LM2931CDR2

LM2931CDR2G LM2931CT LM2931CTG LM2931D2T-5.0 LM2931D2T-5.0G LM2931D2T-5.0R4 LM2931D2T
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